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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38910 Bernin (FR).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **NEYRET, Eric** [FR/FR]; 2, rue Lesdiguières, F-38360 Sassenage (FR). **MALLEVILLE, Christophe** [FR/FR]; 90, rue du Château, F-38660 La Terrasse (FR).

(74) Agent: **MARTIN, Jean-Jacques**; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

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(54) Title: A METHOD OF RAPIDLY THERMALLY ANNEALING MULTILAYER WAFERS WITH AN EDGE

(57) Abstract: The invention provides a method of thermally treating a multilayer wafer (10) with an edge, the wafer being made of materials selected from semiconductive materials and the method being characterized in that during annealing heating is adapted locally and selectively at the edge to take account of the local difference in heat absorption by the edge.

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